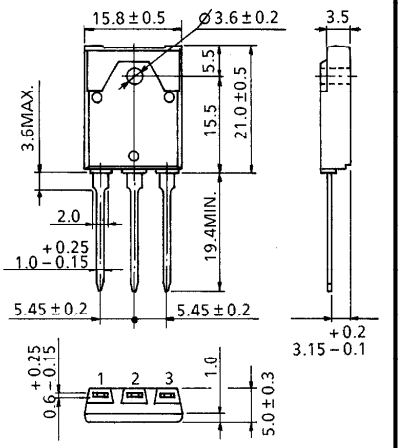
TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2467-Y

HIGH POWER AMPLIFIER APPLICATION

Unit in mm



1. GATE
2. DRAIN
3. SOURCE

JEDEC	—
EIAJ	—
TOSHIBA	2-16F1B

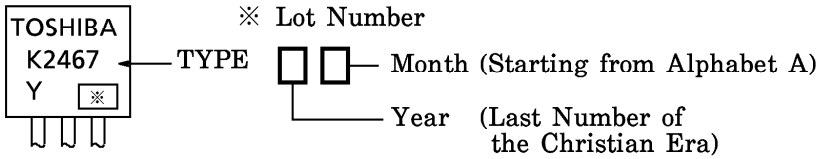
Weight : 5.8g (Typ.)

- High Breakdown Voltage : V_{DSS}=180V
- High Forward Transfer Admittance : $|Y_{fs}|$=4.0S (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	9	A
Drain Power Dissipation (Tc=25°C)	P_D	80	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I_{DSS}	V_{DS}=180V, V_{GS}=0	—	—	1.0	mA
Gate Leakage Current	I_{GSS}	V_{DS}=0, V_{GS}=±20V	—	—	±0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10mA, V_{GS}=0	180	—	—	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	V_{GS}=10V, I_D=6A	—	2.5	5.0	V
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	V_{DS}=10V, I_D=0.1A	1.4	—	2.8	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=10V, I_D=3A	—	4.0	—	S
Input Capacitance	C_{iss}	V_{DS}=30V, V_{GS}=0, f=1MHz	—	700	—	pF
Output Capacitance	C_{oss}	V_{DS}=30V, V_{GS}=0, f=1MHz	—	150	—	pF
Reverse Capacitance	C_{rss}	V_{DS}=30V, V_{GS}=0, f=1MHz	—	90	—	pF

(Note) : $V_{GS(OFF)}$ Classification Y : 1.4~2.8

This transistor is an electrostatic sensitive device.
Please handle with caution.

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